

Abstract of the Disclosure

A method for making magnetic random access memories (MRAM) isolates each and every memory cell in an MRAM array during operation until selected. Some embodiments use series connected diodes for such electrical isolation. Only a selected one of the memory cells will then conduct current between respective ones of the bit and word lines. A better, more uniform distribution of read and data-write data access currents results to all the memory cells. In another embodiment, this improvement is used to increase the number of rows and columns to support a larger data array. In a further embodiment, such improvement is used to increase operating margins and reduce necessary data-write voltages and currents.